



America Semiconductor

Silicon Bridge Rectifier

BR106 thru BR1010

$V_{RRM} = 50\text{ V} - 1000\text{ V}$

$I_F = 10\text{ A}$

Features

- Types up to 1000 V V_{RRM}
- Low forward voltage drop
- Low leakage current

Mechanical Data

Case: Molded plastic body

Polarity: Marked on body

Mounting position: Any

Mounting: Hole for number 6 screw

BR-10 Package



Maximum ratings, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	BR106	BR108	BR1010	Unit
Repetitive peak reverse voltage	V_{RRM}		600	800	1000	V
RMS reverse voltage	V_{RMS}		420	560	700	V
DC blocking voltage	V_{DC}		600	800	1000	V
Continuous forward current	I_F	$T_C \leq 50\text{ }^\circ\text{C}$	10	10	10	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ }^\circ\text{C}$, $t_p = 8.3\text{ ms}$	150	150	150	A
Operating temperature	T_j		-65 to 150	-65 to 150	-65 to 150	$^\circ\text{C}$
Storage temperature	T_{stg}		-65 to 150	-65 to 150	-65 to 150	$^\circ\text{C}$

Electrical characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	BR106	BR108	BR1010	Unit
Diode forward voltage	V_F	$I_F = 5\text{ A}$, $T_j = 25\text{ }^\circ\text{C}$	1.1	1.1	1.1	V
Reverse current	I_R	$V_R = 50\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$ $V_R = 50\text{ V}$, $T_j = 100\text{ }^\circ\text{C}$	10 1000	10 1000	10 1000	μA

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		9.40	9.40	9.40	$^\circ\text{C}/\text{W}$
-------------------------------------	------------	--	------	------	------	---------------------------





FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

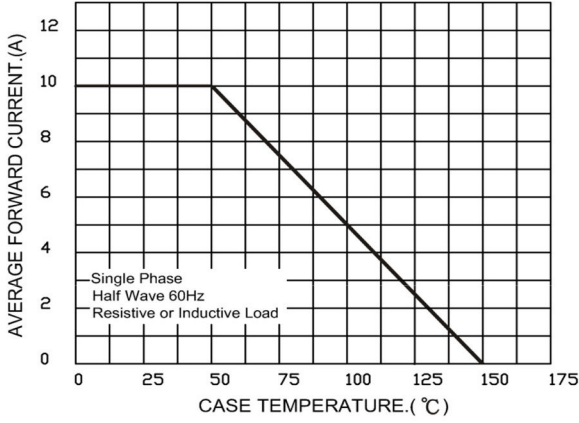


FIG.2-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

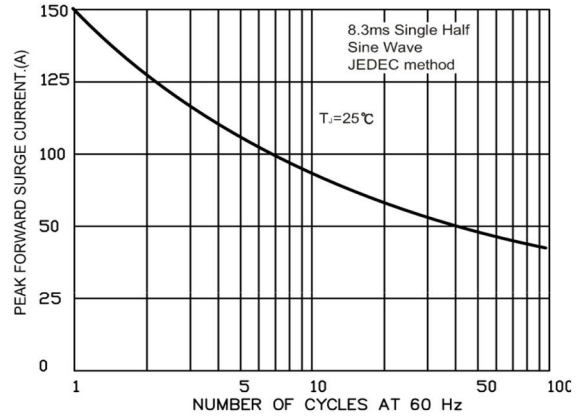


FIG.3-TYPICAL FORWARD CHARACTERISTICS

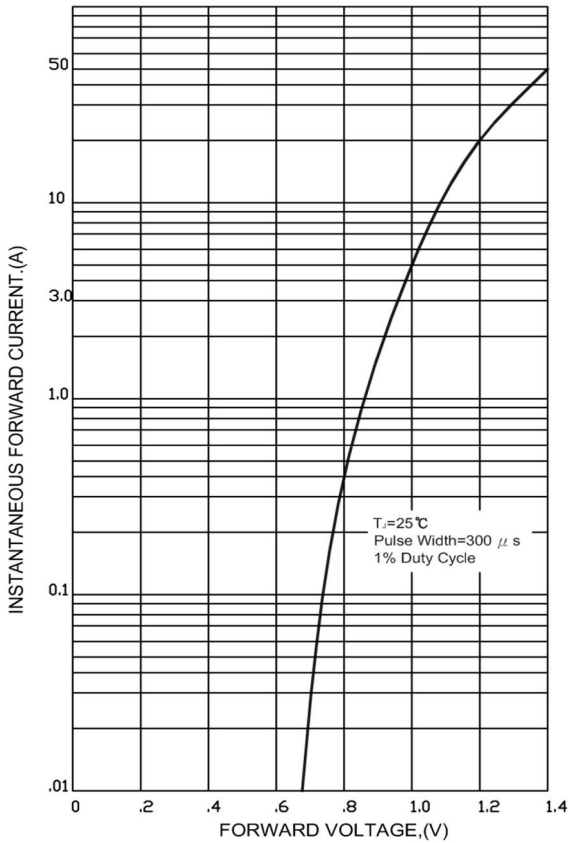


FIG.4-TYPICAL REVERSE CHARACTERISTICS

